

Supplementary Material Information (SMI) for “Effect of Al doping on the microwave absorption performance of 1T/2H heterogeneous interface MoSe₂”

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Table S1 The specific surface area (S_{BET}) and pore volume (V_{pore}) for all prepared samples

Sample	AM00	AM01	AM02	AM03	AM04
S_{BET} (m ² /g)	28.156	30.890	32.610	45.161	23.404
V_{pore} (cm ³ /g)	0.106	0.140	0.137	0.227	0.127

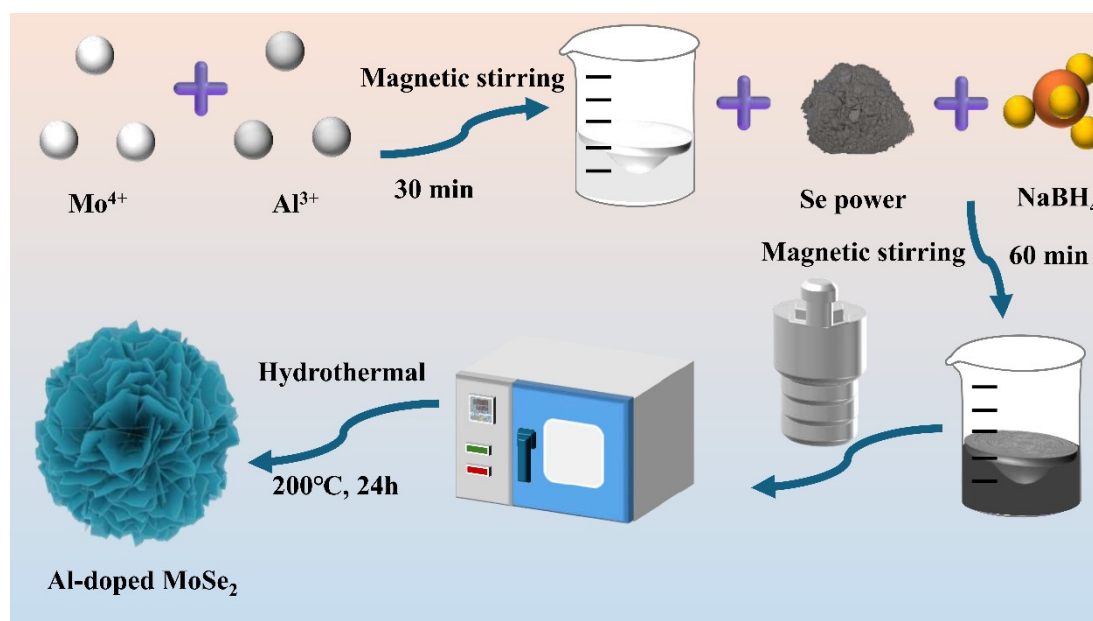


Fig. S1. Schematic diagram of the synthesis process for the Al-doped MoSe₂.

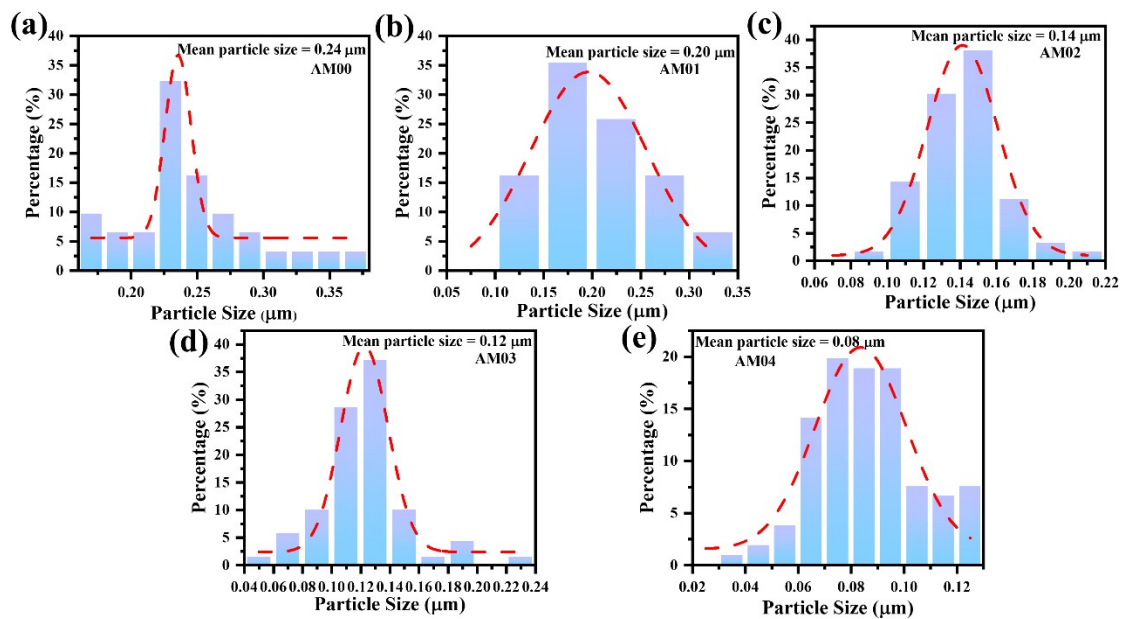


Fig. S2. Statistical chart of particle size of (a) AM00, (b) AM01, (c) AM02, (d) AM03, and (e) AM04

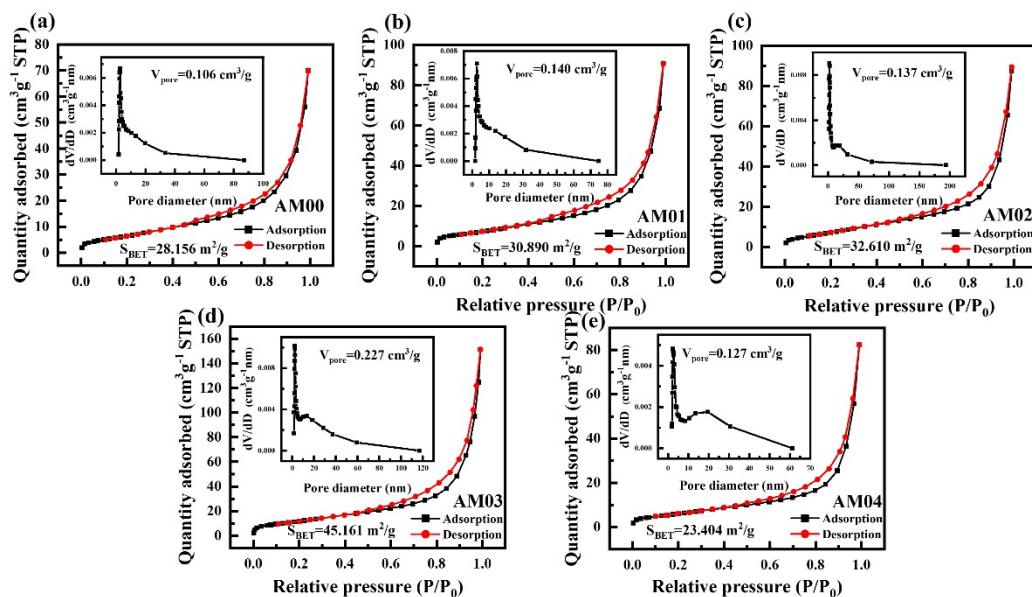


Fig. S3. N₂ adsorption-desorption isotherm and pore size distribution of all prepared samples

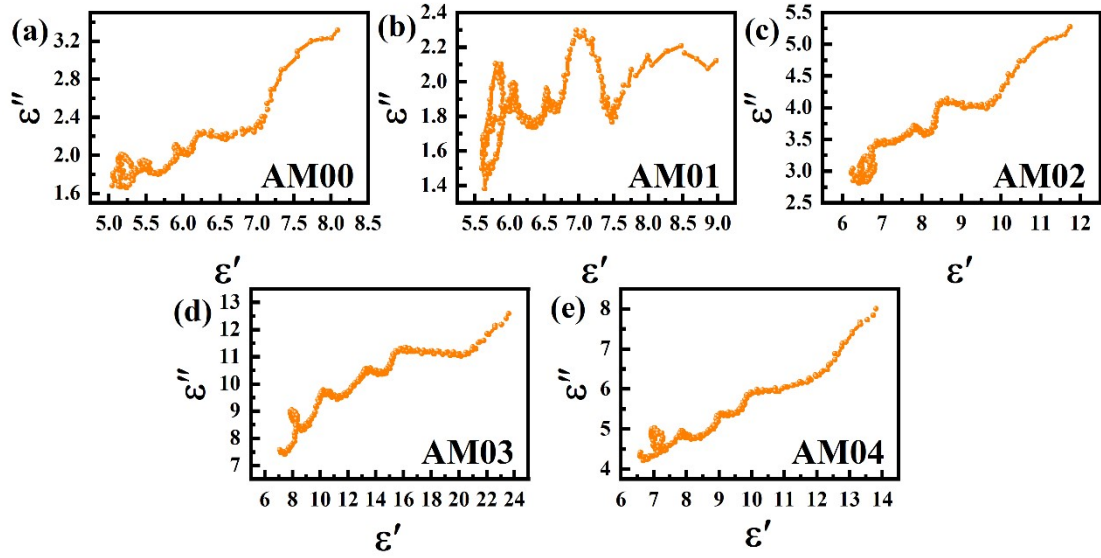


Fig. S4. Cole-Cole plots for all five samples

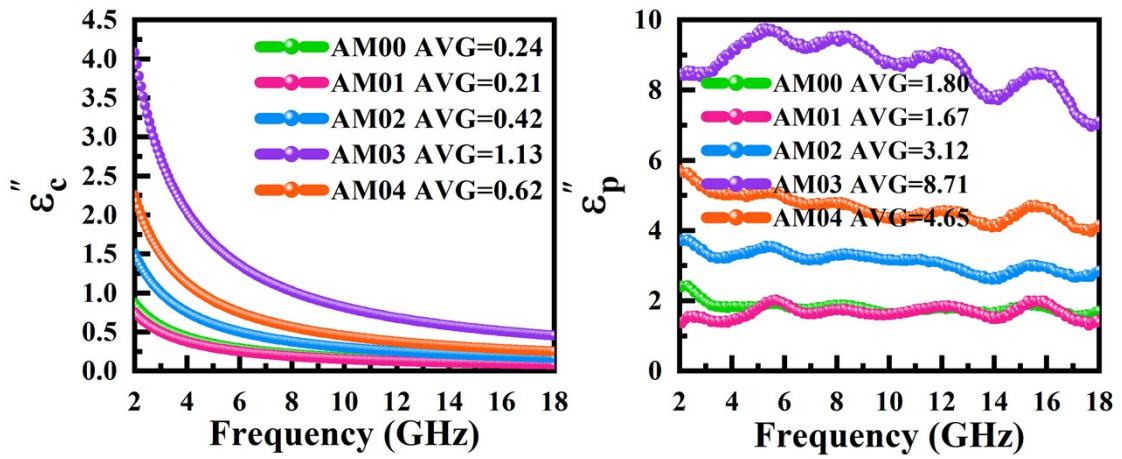


Fig. S5. Conductive loss (ϵ_c'') and polarization loss (ϵ_p'') values for all prepared samples

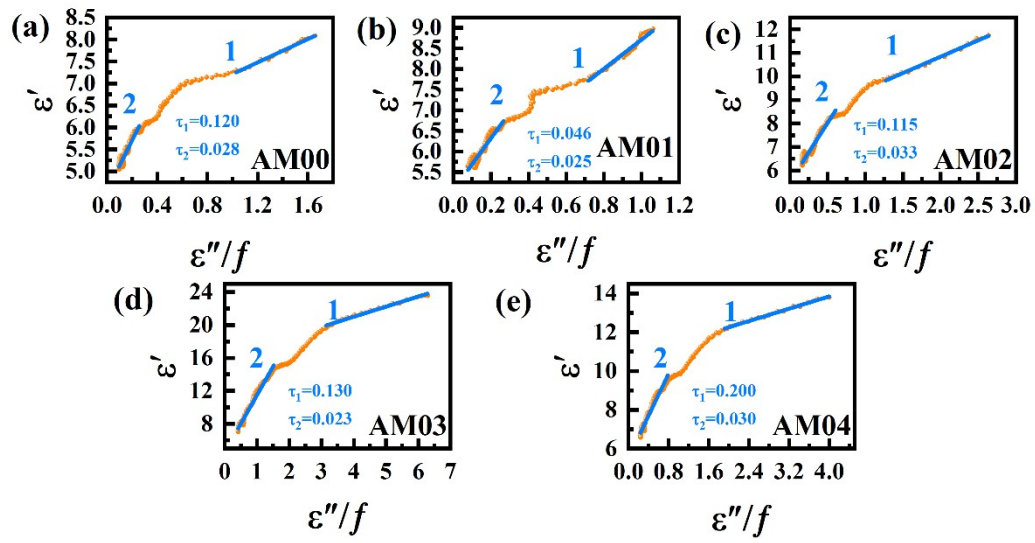


Fig. S6. ϵ'/ϵ'' - f plots for all five samples